





Differential capacitance as a method of determining the presence of a quasi-bidimensional electronic gas

J.C. Martínez-Orozco ^a  , L.M. Gaggero-Sager ^a  , Stoyan J. Vlaev ^b

Show more 

+ Add to Mendeley  Share  Cite

<https://doi.org/10.1016/j.sse.2004.04.010>

[Get rights and content](#)

Abstract

We present the differential capacitance profile for the delta-doped field effect transistor (δ -FET) in a GaAs matrix with both the presence and absence of a two-dimensional electronic gas produced by the delta-doped quantum well.

We demonstrate that in the absence of any quantum well background